

N Channel Power MOSFET

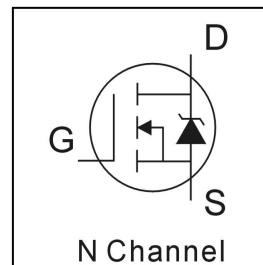
Chip Specification

General Description:

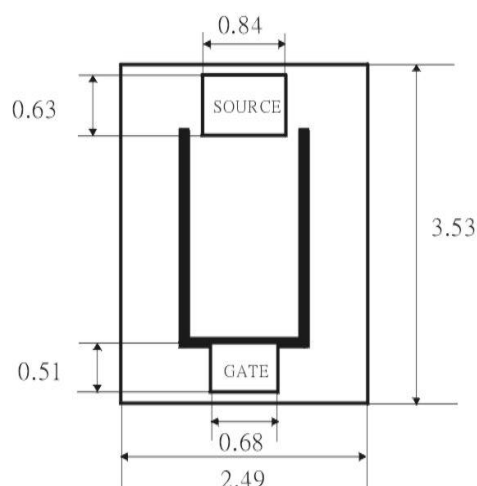
- * Advanced Process Technology
- * Dynamic dV/dt Rating
- * 150°C Operating Temperature
- * Fast Switching
- * Fully Avalanche Rated

Mechanical Data:

D10	
Dimension	2.49mm x 3.53mm
Thickness:	400 µm
Metallization:	
Top :	Al
Backside :	CrNiAg / Au
Suggested Bonding Conditions:	
Die Mounting:	Solder Perform
	95/5 PbSn or 92.5/2.5/5 PbAgIn
Source Bonding Wire:	8 mil Al



D10



600V, N Channel

Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	600	V	VGS=0V, ID=250µA
Static Drain-to - Source On-resistance	RDS(ON)	4.4	Ω	VGS=10V, ID=1.3A
Continuous Drain current (in target package)	ID@25°C	2.2	A	VGS=10V
Continuous Drain current (in target package)	ID@100°C	1.4	A	VGS=10V
Operation Junction	Tj	-55~150	°C	
Storage Temperature	TSTR	-55~150	°C	

Target Device: IRFBC20

TO-220AB

Pd

50

W

@Tc=25°C